

CLAIMS

We claim:

1 1. An apparatus for measuring film stack characteristics of a sample, the
2 apparatus comprising:

3 a beam generator configurable to direct a charged particle beam towards the
4 sample such that the charged particle beam penetrates at least two layers of the
5 film stack, the charged particle beam causing X-rays to emanate from the sample;
6 and

7 a first X-ray detector positioned above the sample so as to detect at least a
8 portion of the X-rays emanating from the sample.

1 2. The apparatus as recited in claim 1 wherein the first X-ray detector is
2 configured to detect X-rays of a specific energy level.

1 3. The apparatus as recited in claim 1 wherein the first X-ray detector is a
2 wavelength dispersive system.

1 4. The apparatus as recited in claim 3 wherein the wavelength dispersive system
2 contains a reflective surface and a sensor, the reflective surface configured to direct
3 X-rays of a predetermined energy level to the sensor.

1 5. The apparatus as recited in claim 1 further comprising a second X-ray
2 detector, wherein the first and second X-ray detectors are wavelength dispersive
3 systems.

1 6. The apparatus as recited in claim 1 wherein a conductive film layer and a liner
2 film layer are two of the at least two layers that are penetrated by the charged particle
3 beam.

4
5 7. The apparatus as recited in claim 1 further comprising a processor linked to
6 the beam generator and to the first X-ray detector.

7
1 8. The apparatus as recited in claim 7 wherein the processor is configured to
2 control the first X-ray detector so that it detects X-rays of a specific energy level.

3 9. The apparatus as recited in claim 7 wherein the processor is configured to
4 control the beam generator so that the charged particle beam directed to the sample
5 penetrates at least a conductive film layer and a liner film layer of the sample.

6 10. An apparatus for measuring film stack characteristics of a sample, the
7 apparatus comprising:

8 a beam generator configurable to direct a charged particle beam towards the
9 sample such that the charged particle beam penetrates at least two layers of the film
10 stack, the charged particle beam causing X-rays to emanate from the sample; and

11 at least two X-ray detectors positioned above the sample so as to detect at least
12 a portion of the X-rays emanating from the sample, each of the X-ray detectors
13 configured to detect X-rays having a specific energy level.

14 11. A method for measuring at least one characteristic of a film stack on a sample,
15 the method comprising:

16 directing a charged particle beam towards the sample such that the charged
17 particle beam penetrates at least two layers of the film stack, the charged particle
18 beam causing X-rays to emanate from the sample; and

19 detecting at least a portion of the X-rays emanating from the sample using a
20 first X-ray detector which is positioned above the sample.

9

1 12. The method for measuring as recited in claim 11, further comprising
2 configuring the first X-ray detector to detect X-rays of a specific energy level.

3

1 13. The method for measuring as recited in claim 11 wherein the first X-ray
2 detector is a wavelength dispersive system.

3

1 14. The method for measuring as recited in claim 13 further comprising
2 positioning a reflective surface contained within the wavelength dispersive system in
3 an orientation to direct X-rays of a predetermined energy level to a sensor contained
4 within the wavelength dispersive system.

5

1 15. The method for measuring as recited in claim 11 further comprising detecting
2 at least a portion of the X-rays emanating from the sample using a second X-ray
3 detector, wherein the first and second X-ray detectors are wavelength dispersive
4 systems.

5

1 16. The method for measuring as recited in claim 11, the method further
2 comprising selecting a charged particle beam energy and a charged particle beam
3 current at which the charged particle beam will be produced.

4

1 17. The method for measuring as recited in claim 11, the method further
2 comprising:

3 collecting data resulting from the detected X-rays; and
4 analyzing the data to determine film stack characteristics.

5

1 18. The method for measuring as recited in claim 11 wherein a conductive film
2 layer and a liner film layer are two of the at least two layers that are penetrated by the
3 charged particle beam.
4

5 19. A computer-readable medium comprising computer code for measuring at
6 least one characteristic of a film stack on an sample, the computer-readable medium
7 comprising:

8 selecting a charged particle beam energy and a charged particle beam current
9 at which a charged particle beam will be produced;

10 controlling the charged particle beam which is directed towards the sample
11 such that the charged particle beam penetrates at least two layers of the film stack, the
12 charged particle beam causing X-rays to emanate from the sample;

13 receiving data from at least two X-ray detectors, each of the X-ray detectors
14 configured to detect at least a portion of the X-rays emanating from the sample; and

15 analyzing the data to determine one or more film stack characteristics.
16

1 20. The computer-readable medium as recited in claim 19 wherein a conductive
2 film layer and a liner film layer are two of the at least two layers that are penetrated
3 by the charged particle beam.

5 21. A method of determining film stack characteristic values of a sample, the
6 method comprising:

7 obtaining raw data related to the film stack characteristic values from a
8 wavelength dispersive system which detects X-rays emanating from the sample;

9 selecting a set of estimated film stack characteristic values;

10 obtaining predicted data by solving equations which model a film stack
11 configuration using the set of estimated film stack characteristic values;

12 comparing the predicted data against the raw data;

B3
Cm J. d

13 selecting a new set of estimated film stack characteristic values when the
14 difference between the predicted data and the raw data is larger than a predetermined
15 margin of error; and

16 obtaining a new set of predicted data by solving equations which model the
17 film stack configuration using the new set of estimated film stack characteristic values
18 when the difference between the predicted data and the raw data is larger than the
19 predetermined margin of error.

20

21

1 22. The method of determining film stack characteristic values as recited in claim
2 21 further comprising recording the set of estimated film stack characteristic values
3 when the difference between the predicted data and the raw data is equal to or smaller
4 than the predetermined margin of error.

5

6 23. The method of determining film stack characteristic values as recited in claim
7 21 wherein the raw and predicted data represent a count value of X-rays having a
8 specific energy level, the count value being the total number of X-rays received by the
9 wavelength dispersive system over a period of time.

10

1 24. The method of determining film stack characteristic values as recited in claim
2 21 wherein the estimated film stack characteristic values represent a thickness and a
3 composition of at least two layers within the film stack.

4

1 25. The method of determining film stack characteristics as recited in claim 24
2 wherein a conductive layer and a liner layer are two of the at least two layers within
3 the film stack.

4

4

1 30. The computer-readable medium as recited in claim 29 wherein a conductive
2 layer and a liner layer are two of the at least two layers of the film stack.

3

Add
C1

add
at